

FIG. 1

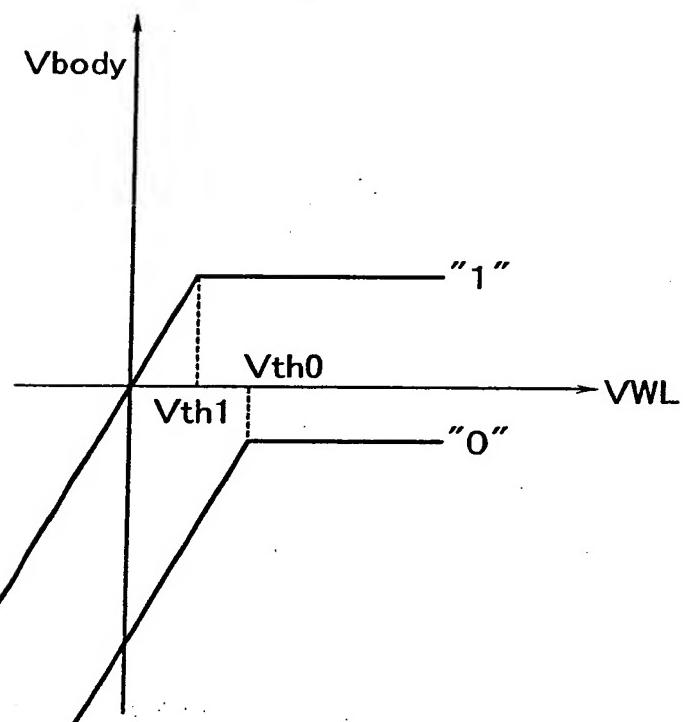


FIG. 2

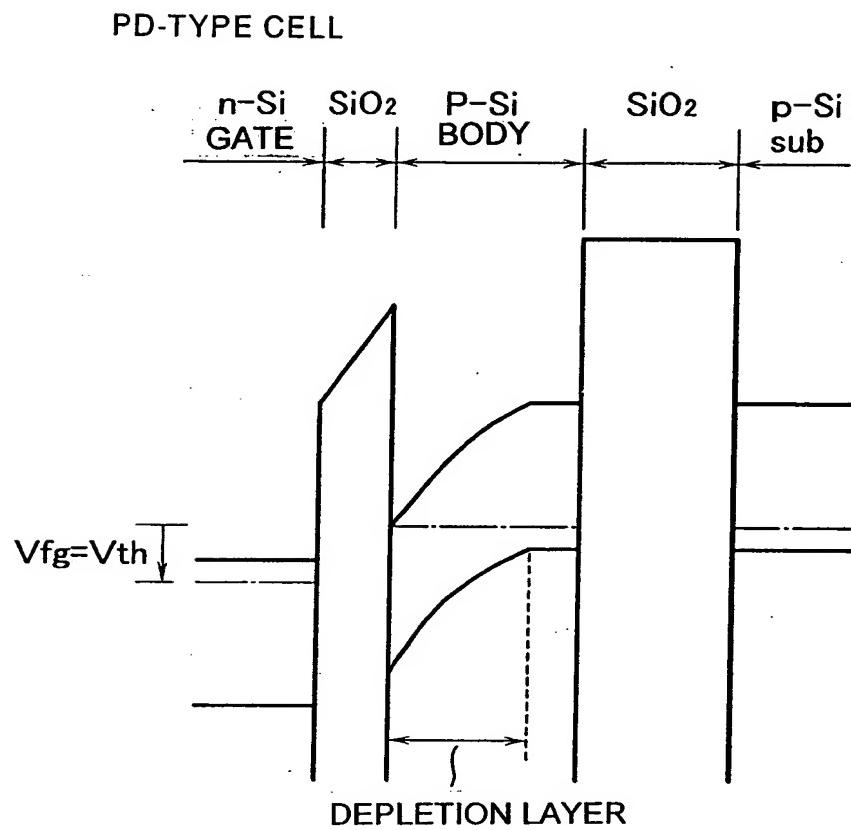


FIG. 3

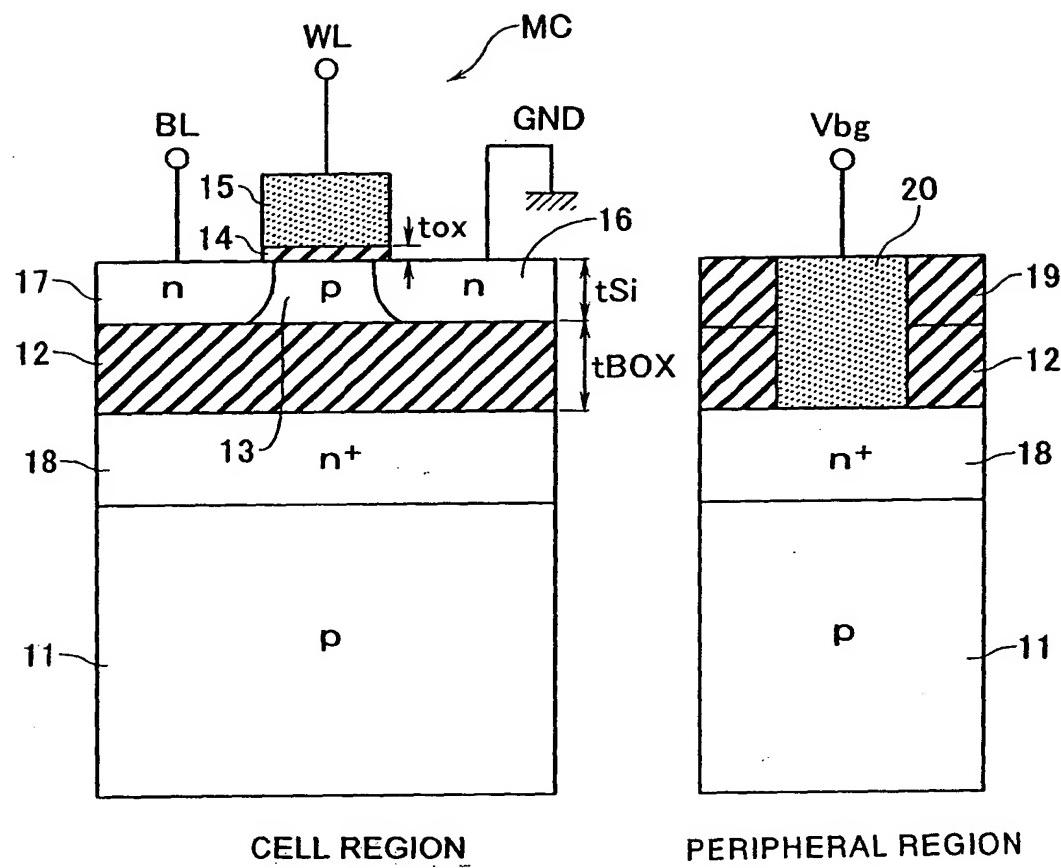


FIG. 4A

FIG. 4B

FD-TYPE CELL

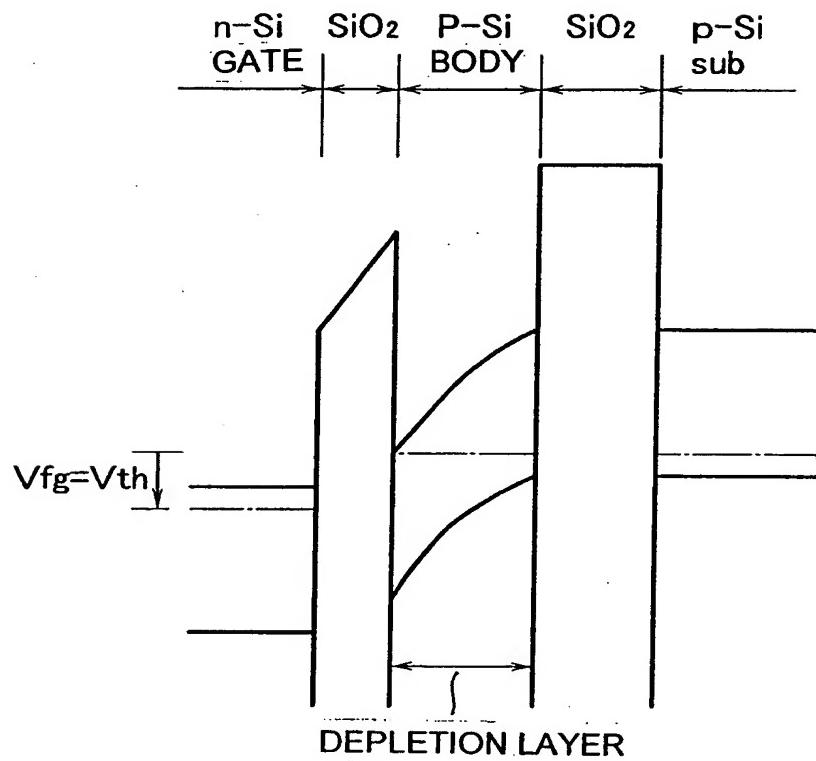


FIG. 5

"0" STATE OF FD-TYPE CELL

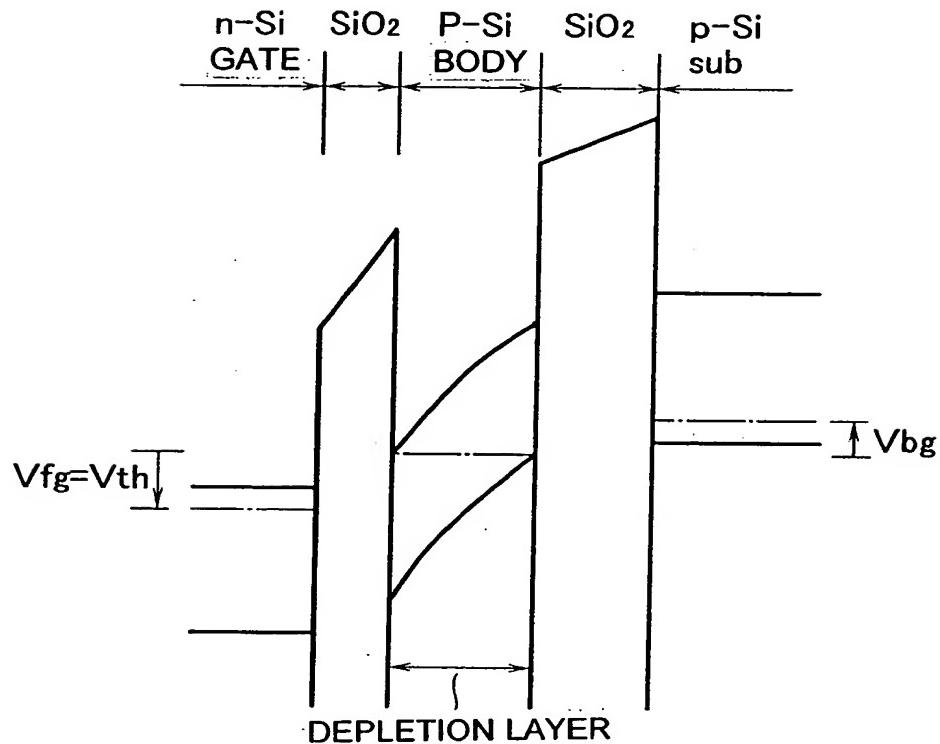


FIG. 6

$t_{ox}=10\text{nm}$, $t_{BOX}=30\text{nm}$, $t_{Si}=25\text{nm}$, $NA=1.0e15\text{cm}^{-3}$

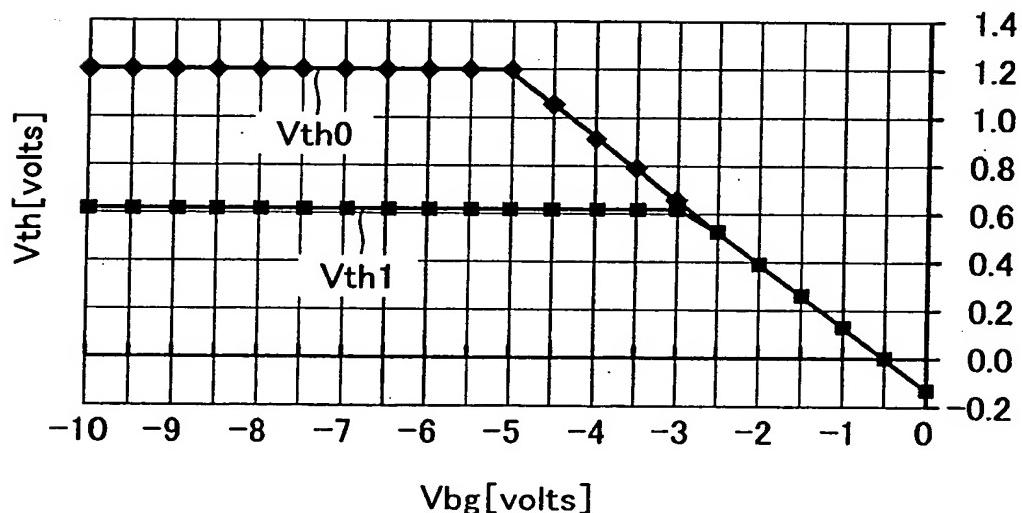


FIG. 7

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"O" write/read

($t_{ox}=10\text{nm}$, $t_{BOX}=30\text{nm}$, $t_{Si}=25\text{nm}$,
 $V_{bg}=-5V$, $N_A=1.0e15\text{cm}^{-3}$)

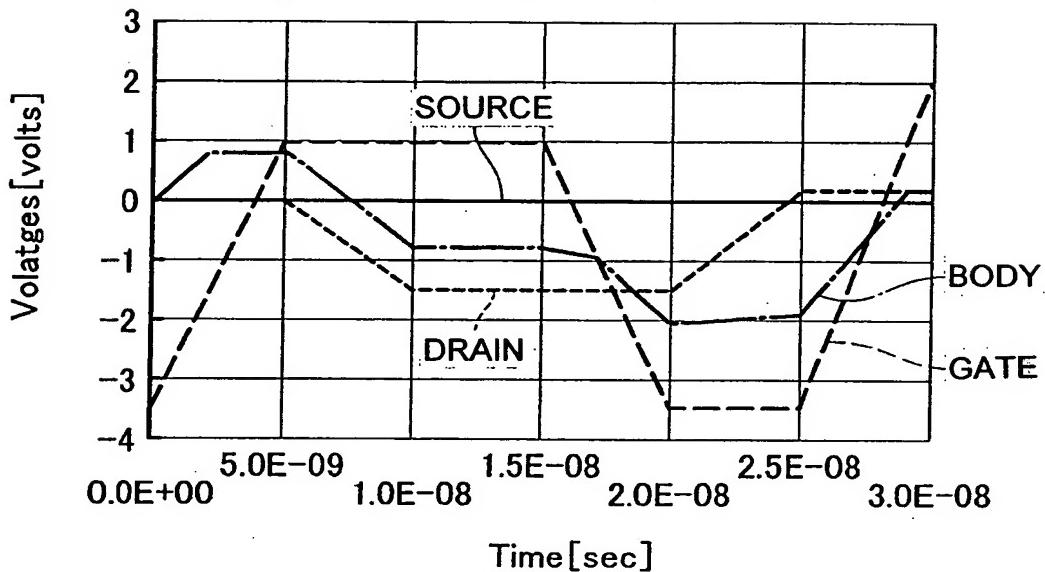


FIG. 8

"1" write/read

($t_{ox}=10\text{nm}$, $t_{BOX}=30\text{nm}$, $t_{Si}=25\text{nm}$,
 $V_{bg}=-5V$, $N_A=1.0e15\text{cm}^{-3}$)

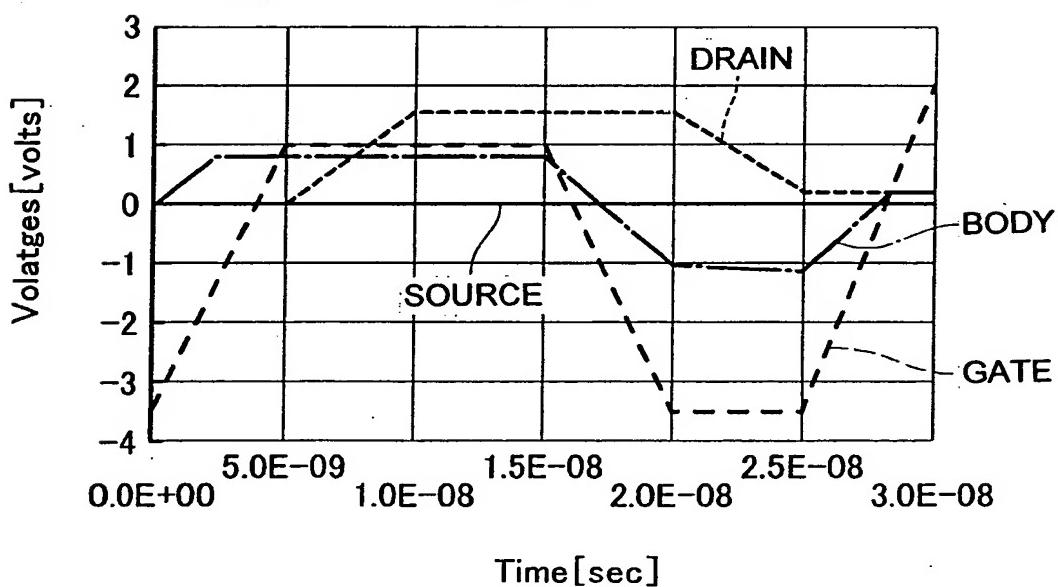


FIG. 9

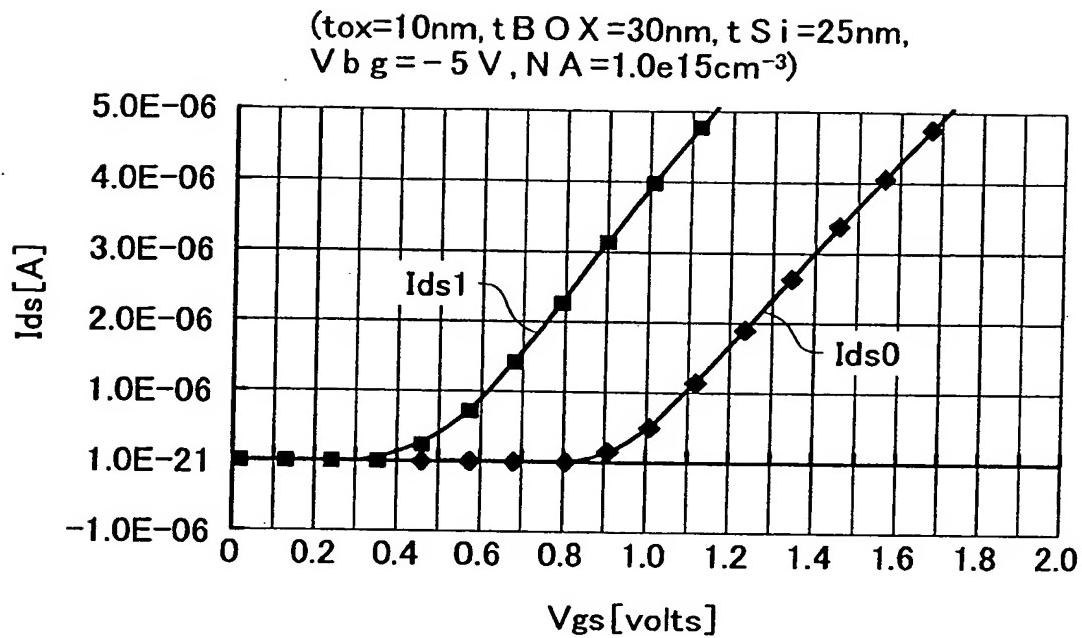


FIG. 10

($t_{ox}=10\text{nm}$, $t_{BOX}=30\text{nm}$, $t_{Si}=25\text{nm}$, $N_A=1.0e15\text{cm}^{-3}$)

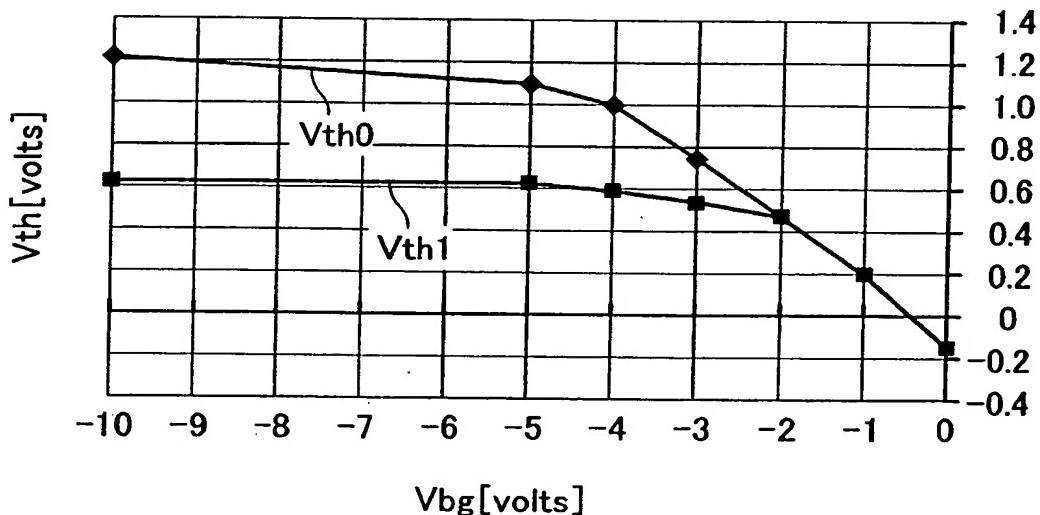


FIG. 11

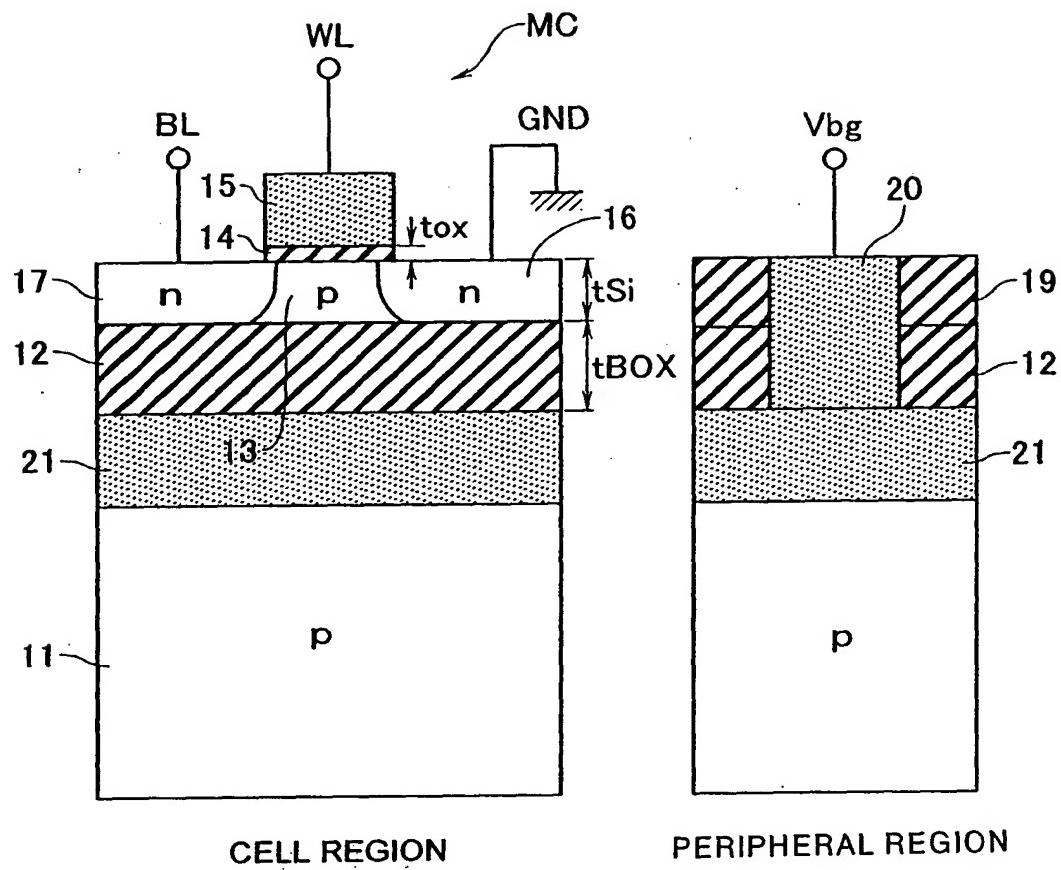


FIG. 12A

FIG. 12B

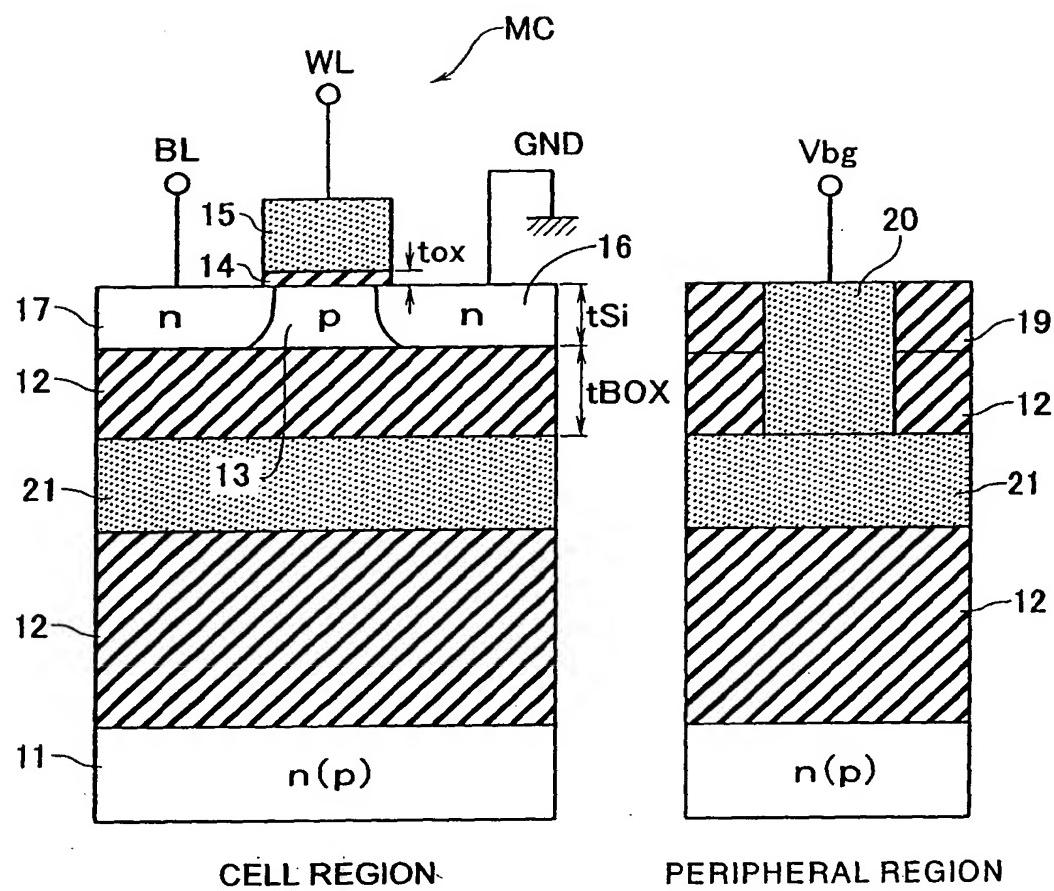


FIG. 13A

FIG. 13B

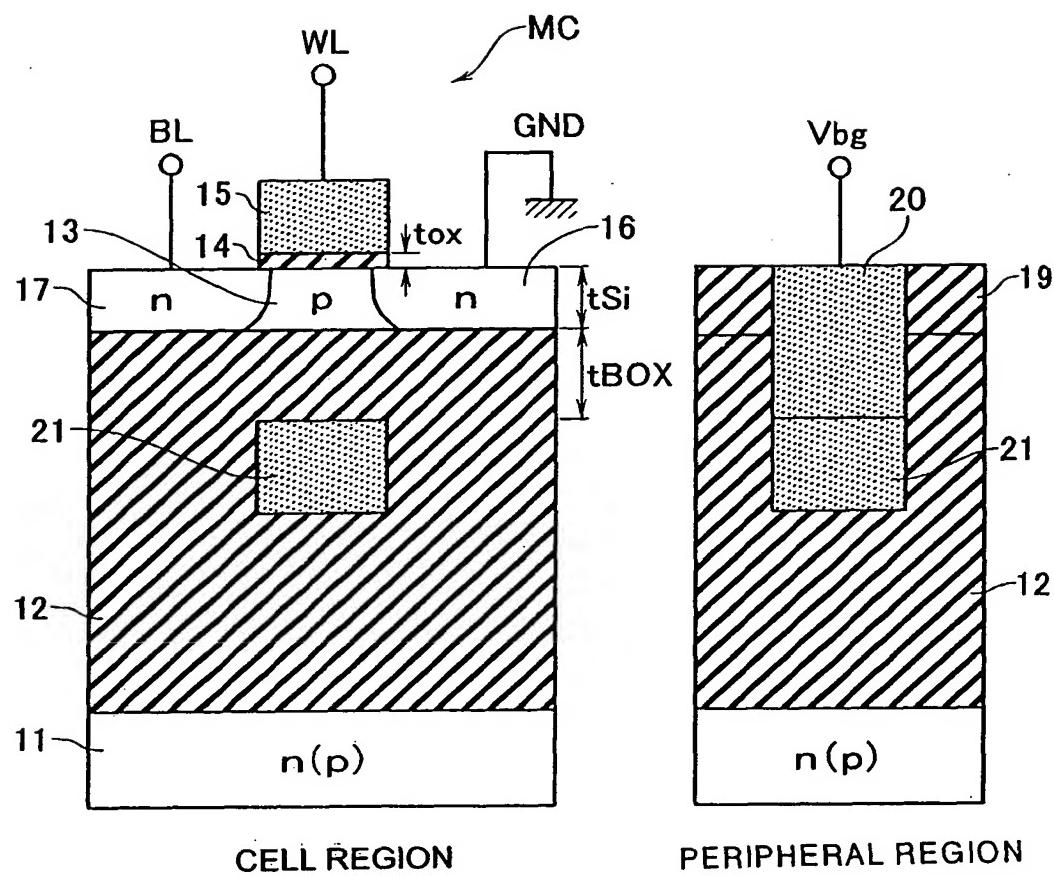


FIG. 14A

FIG. 14B

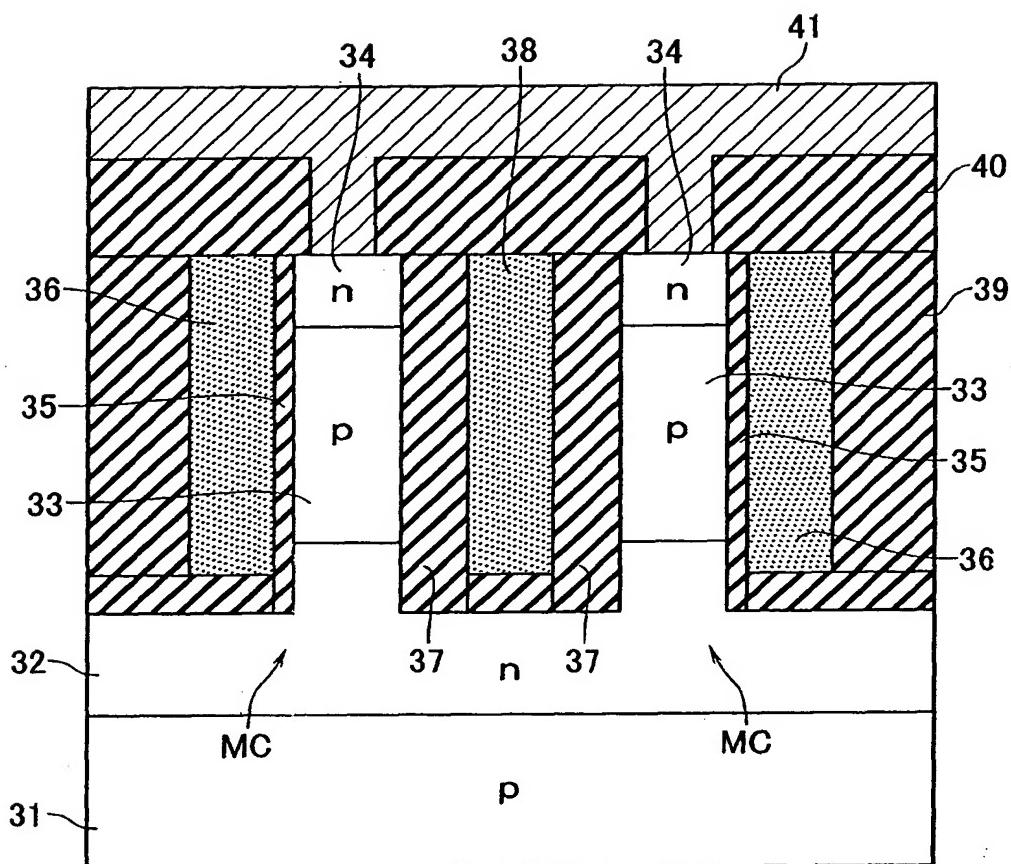


FIG. 15

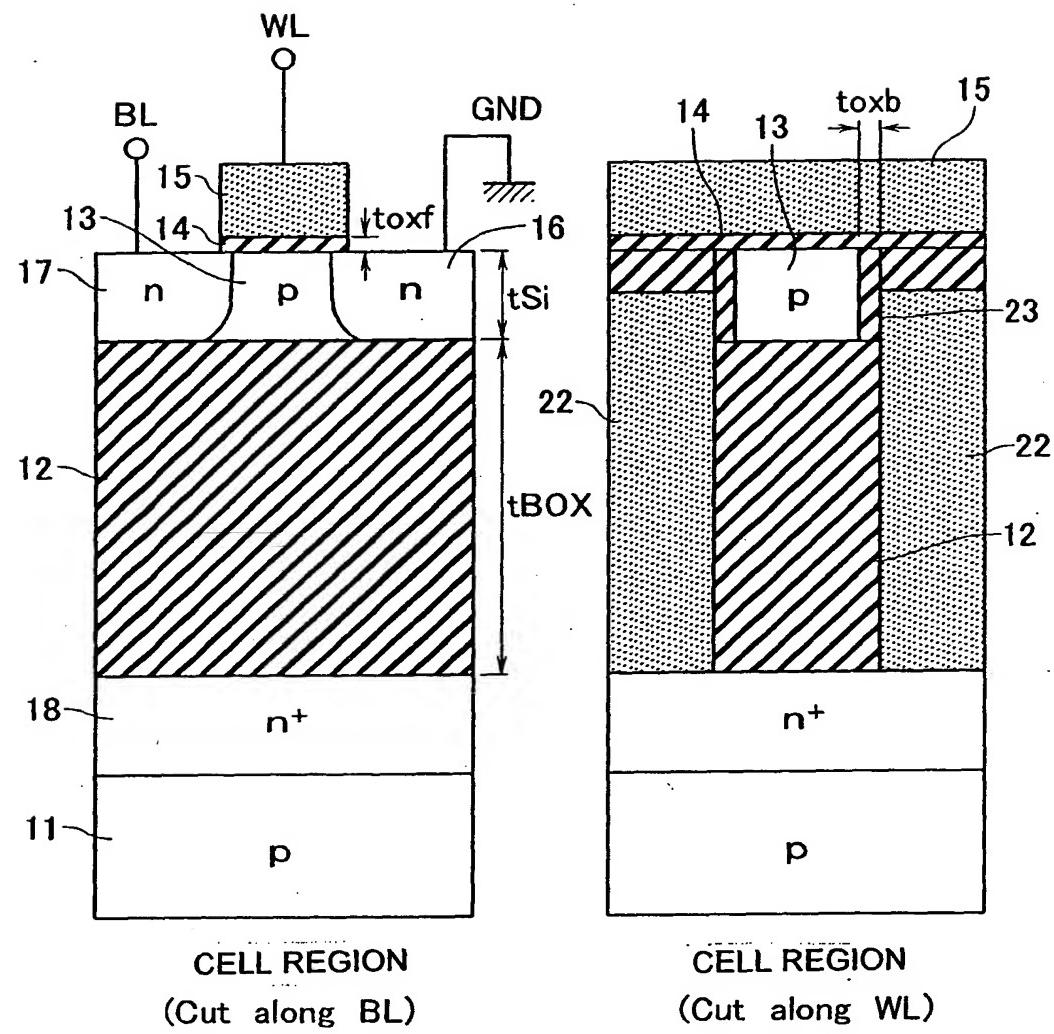


FIG. 16A

FIG. 16B

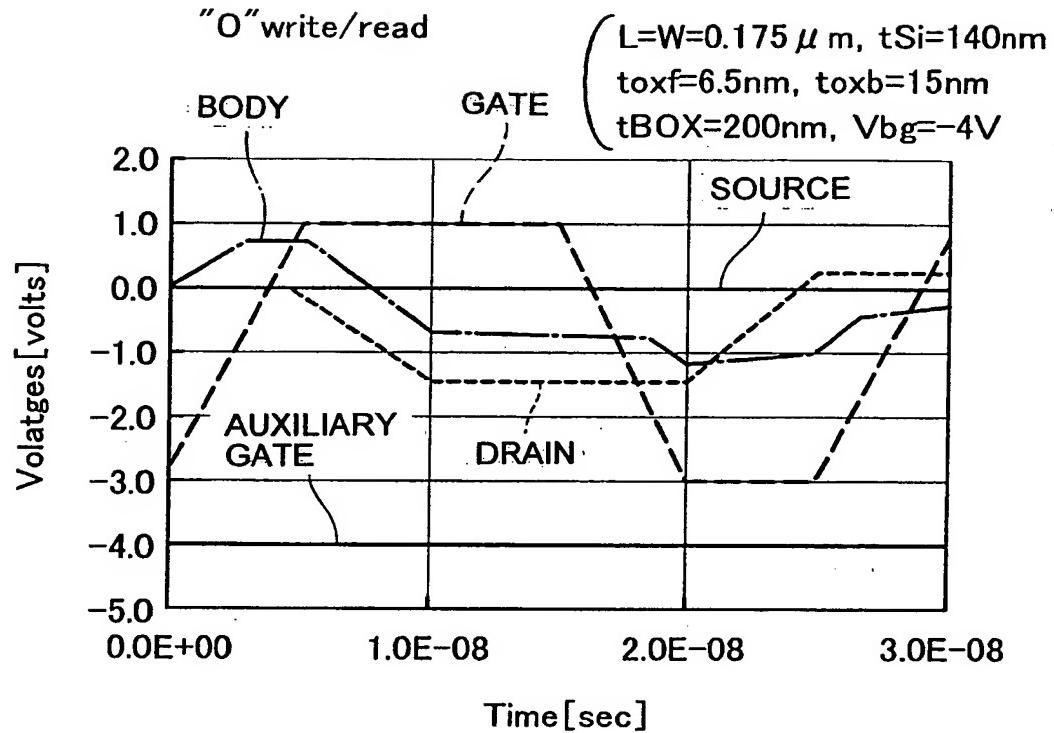


FIG. 17

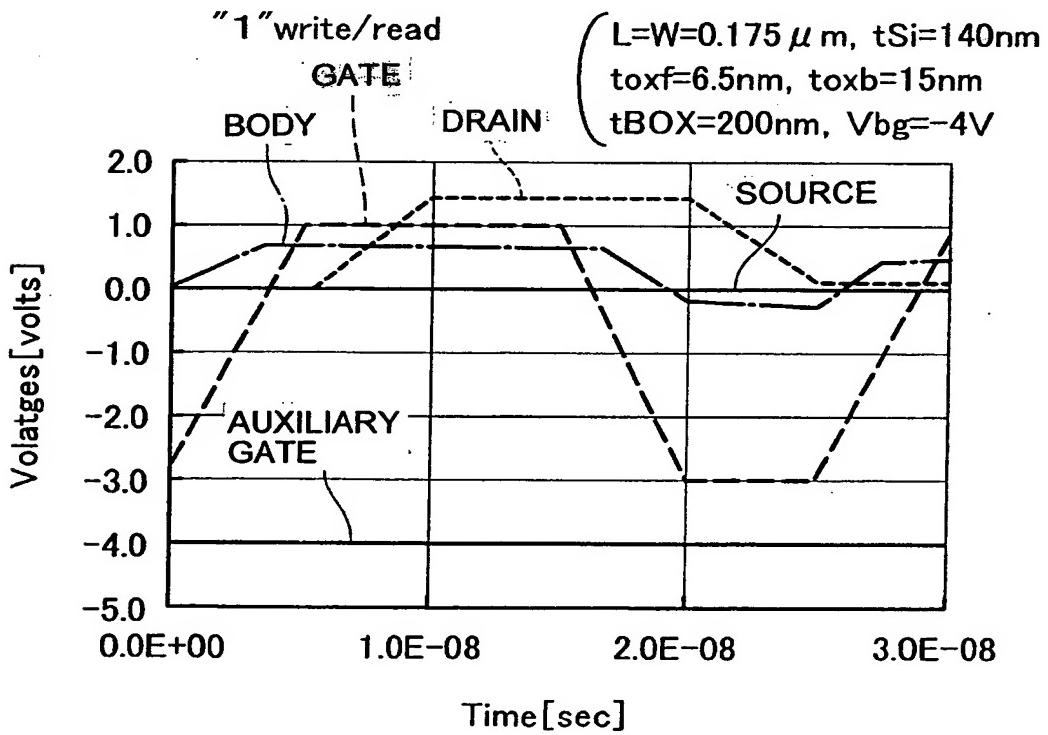


FIG. 18

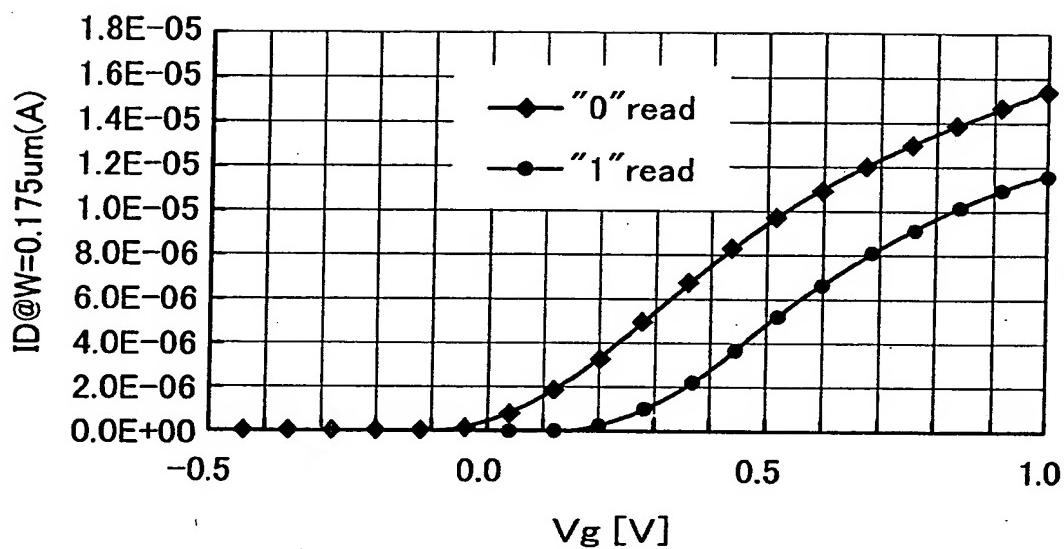


FIG. 19

$t_{ox}=10\text{nm}$, $t_{BOX}=30\text{nm}$, $t_{Si}=25\text{nm}$,
 $NA=ni=1.0e10\text{cm}^{-3}$ @300K,p+poly gate

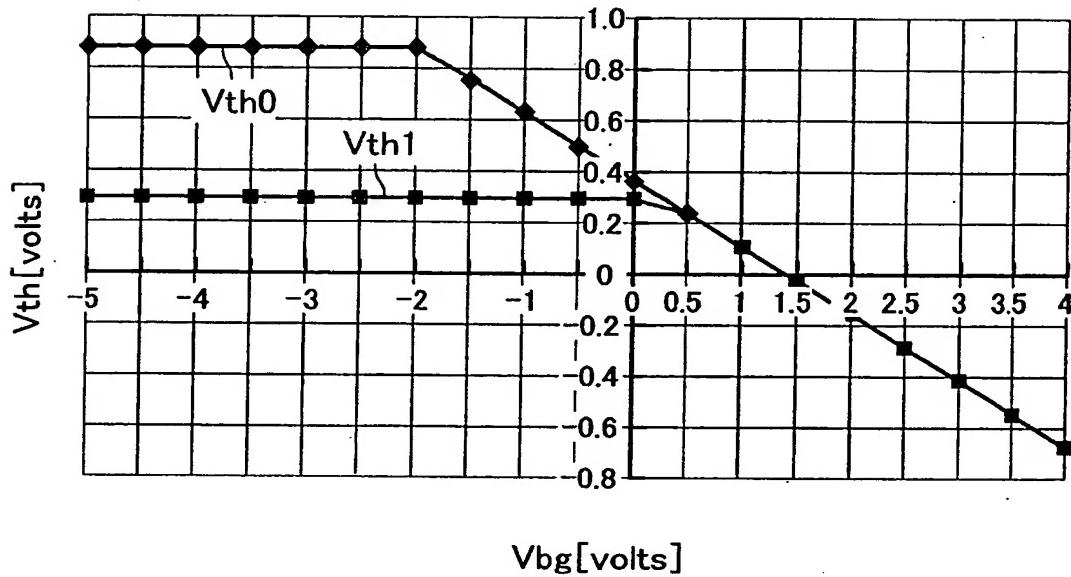


FIG. 20A

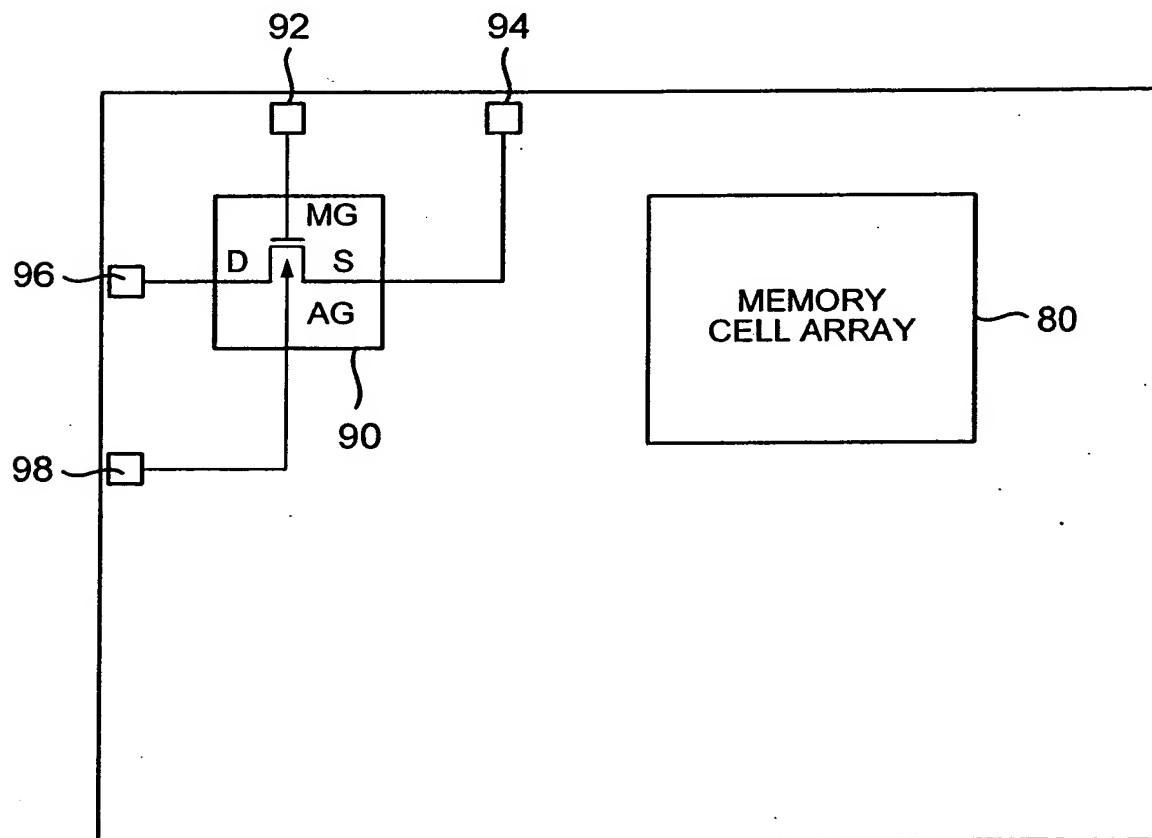


FIG. 20B

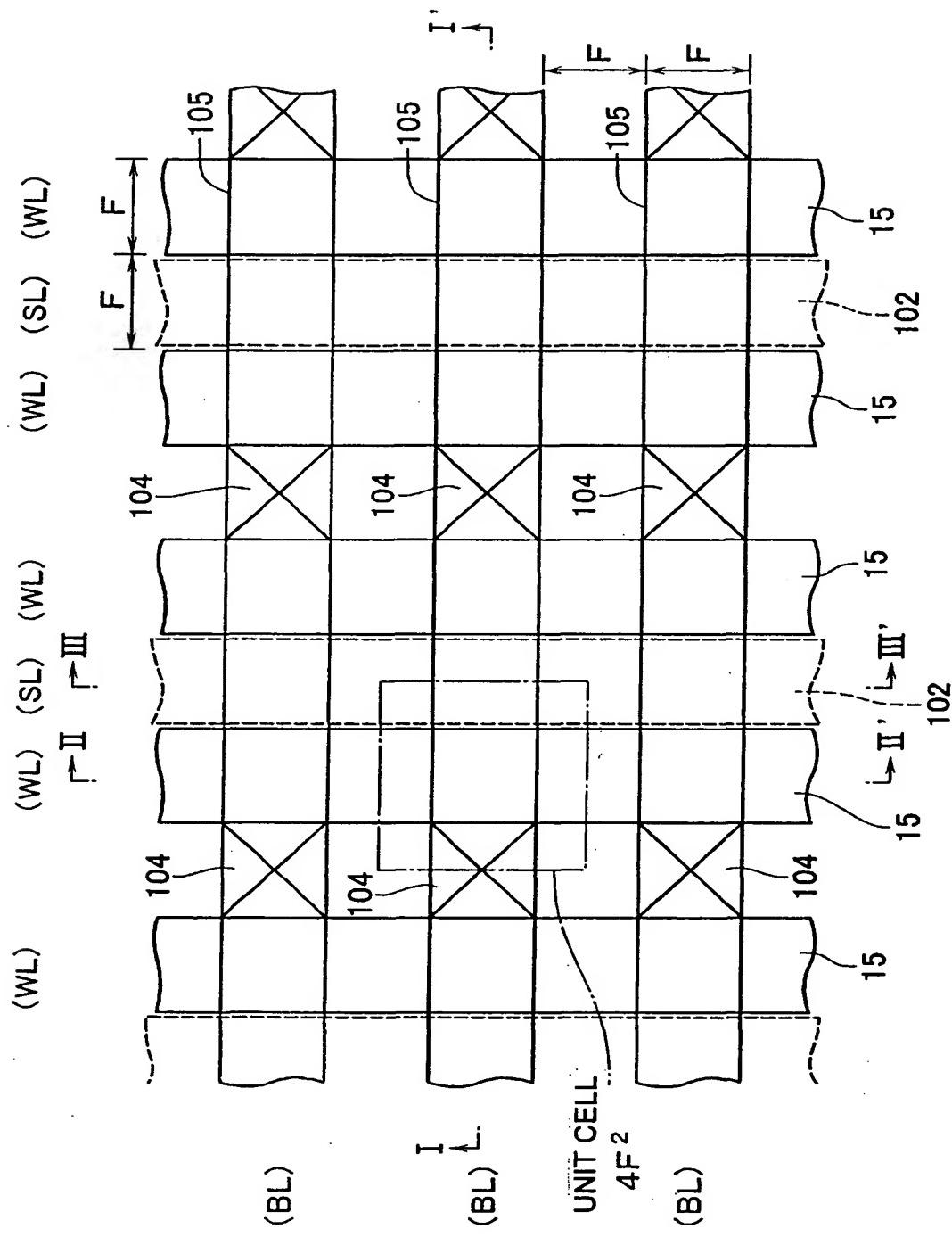


FIG. 21

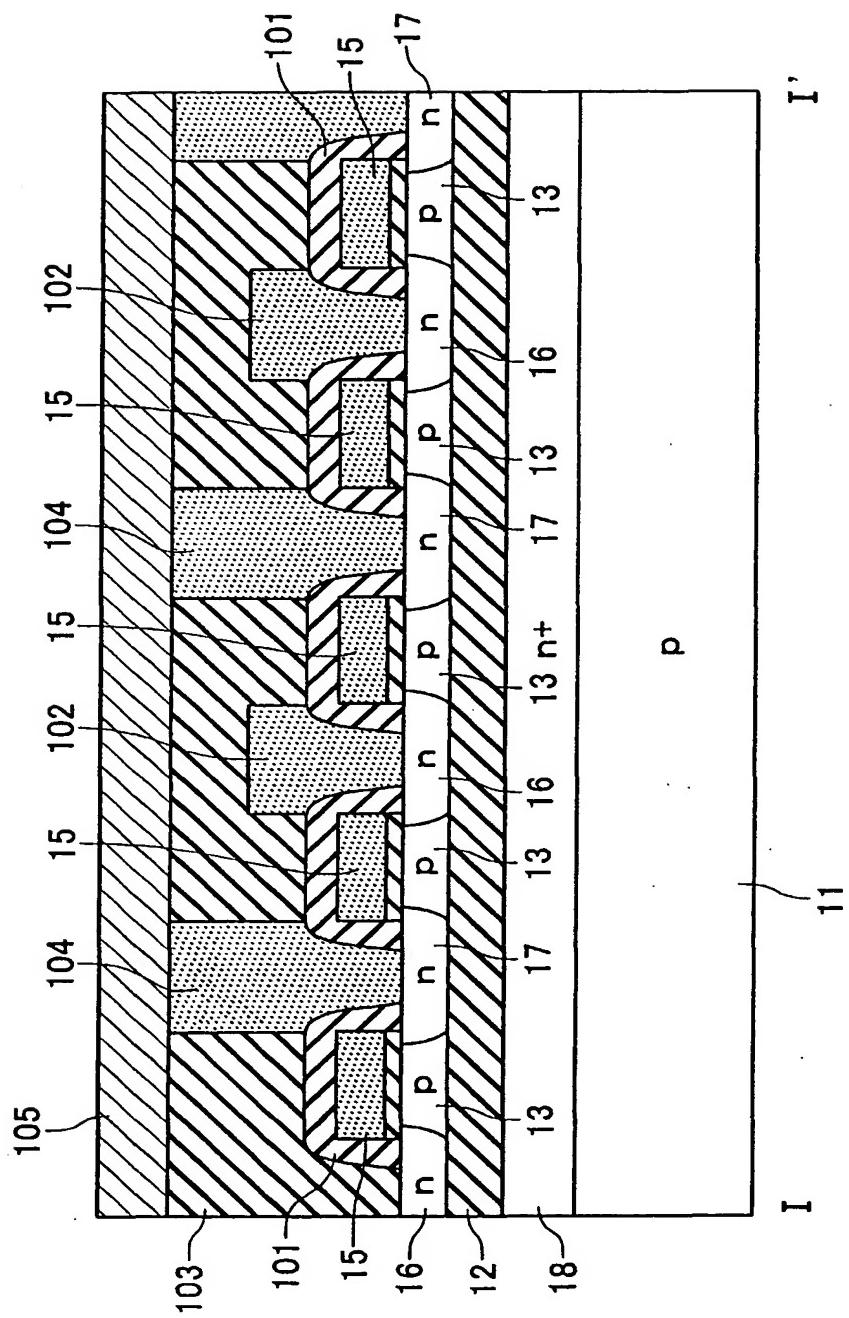


FIG. 22

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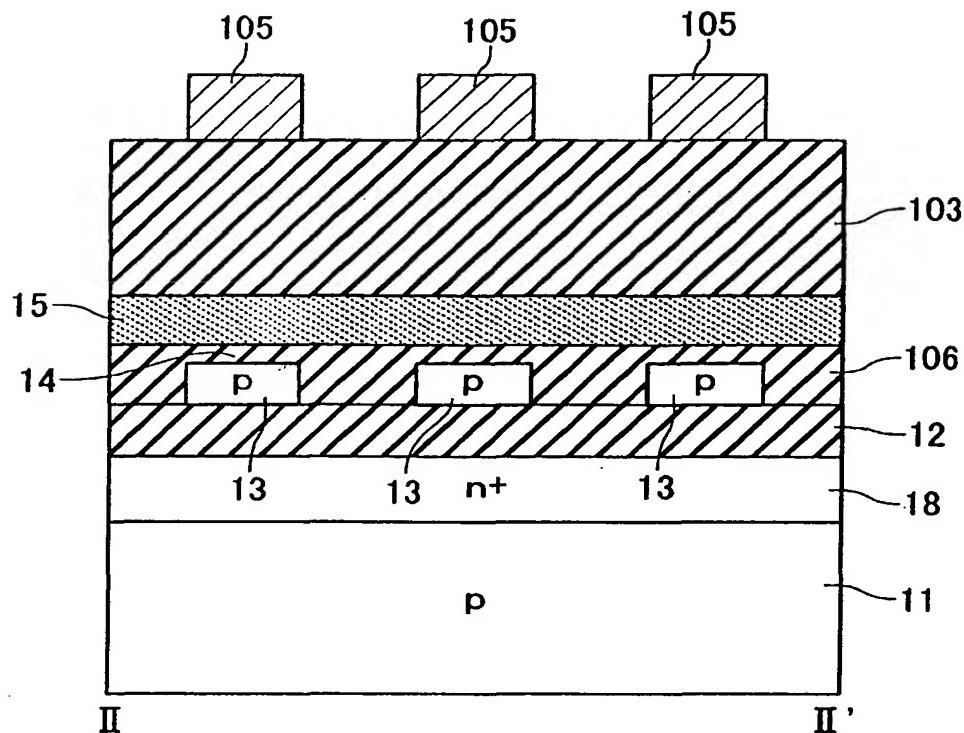


FIG. 23

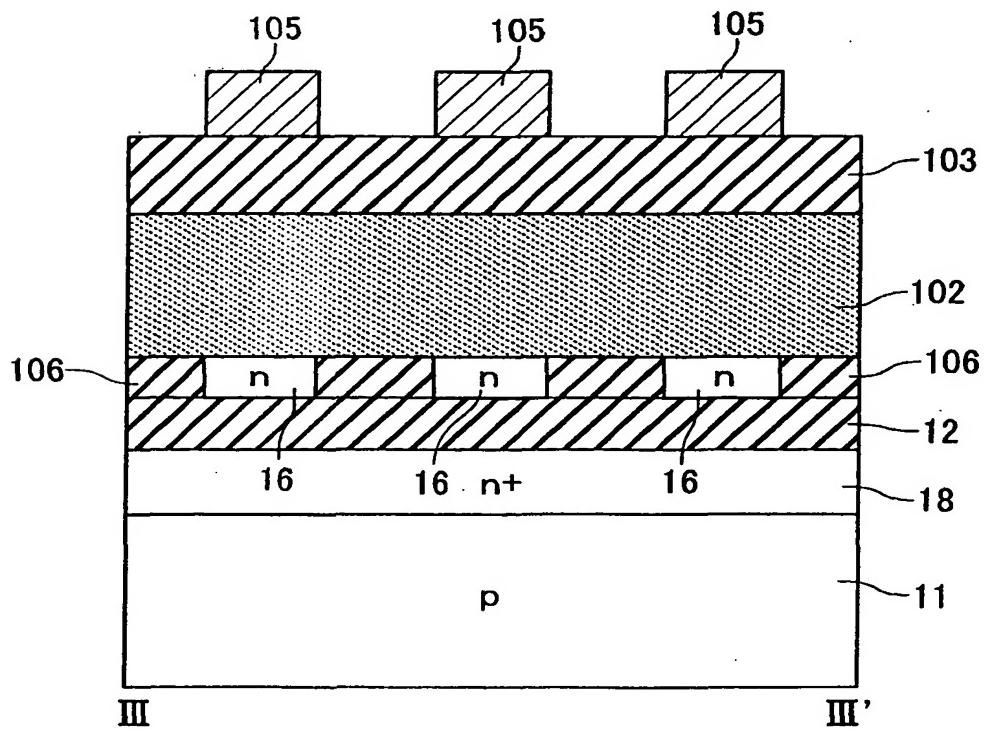


FIG. 24

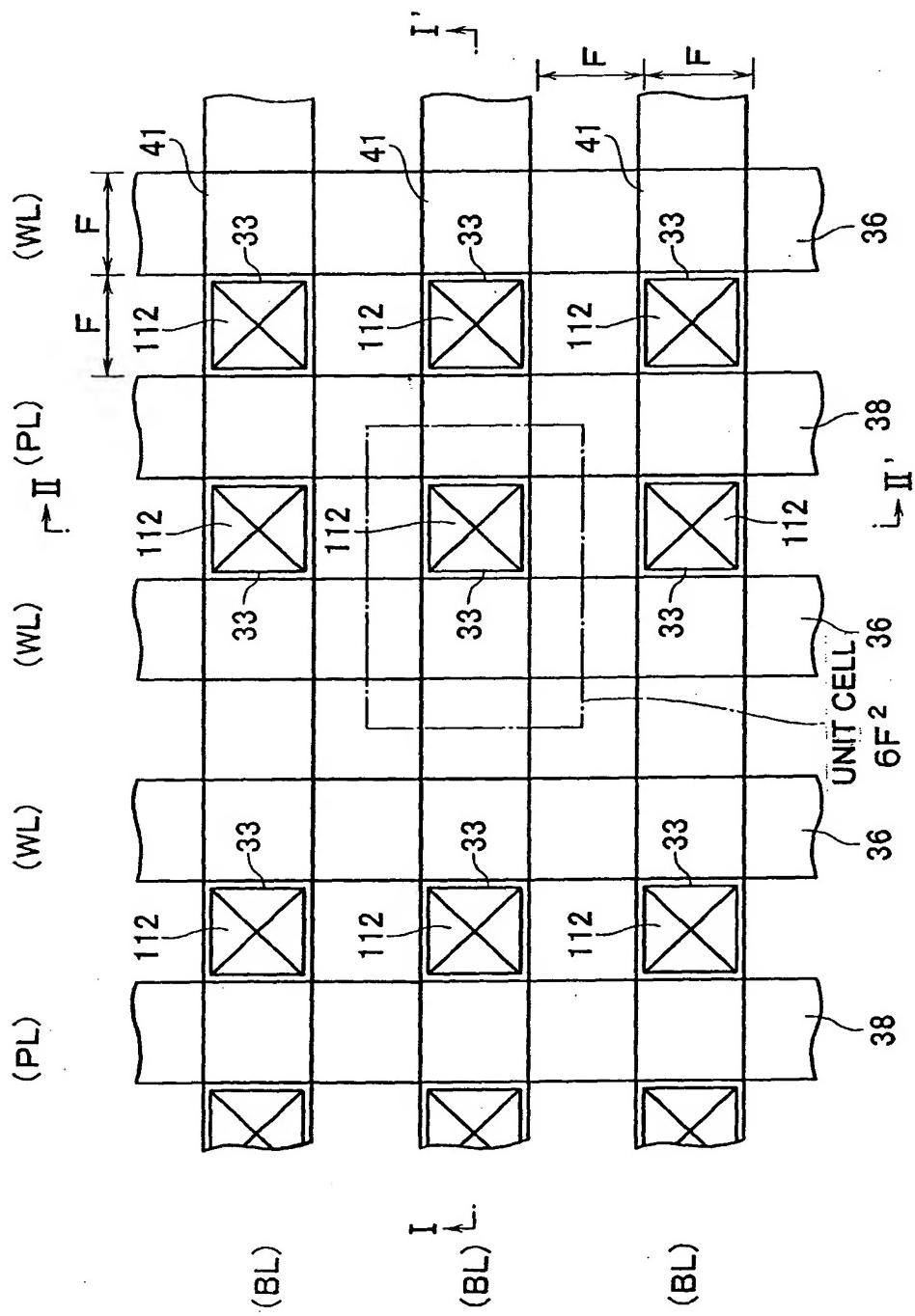


FIG. 25

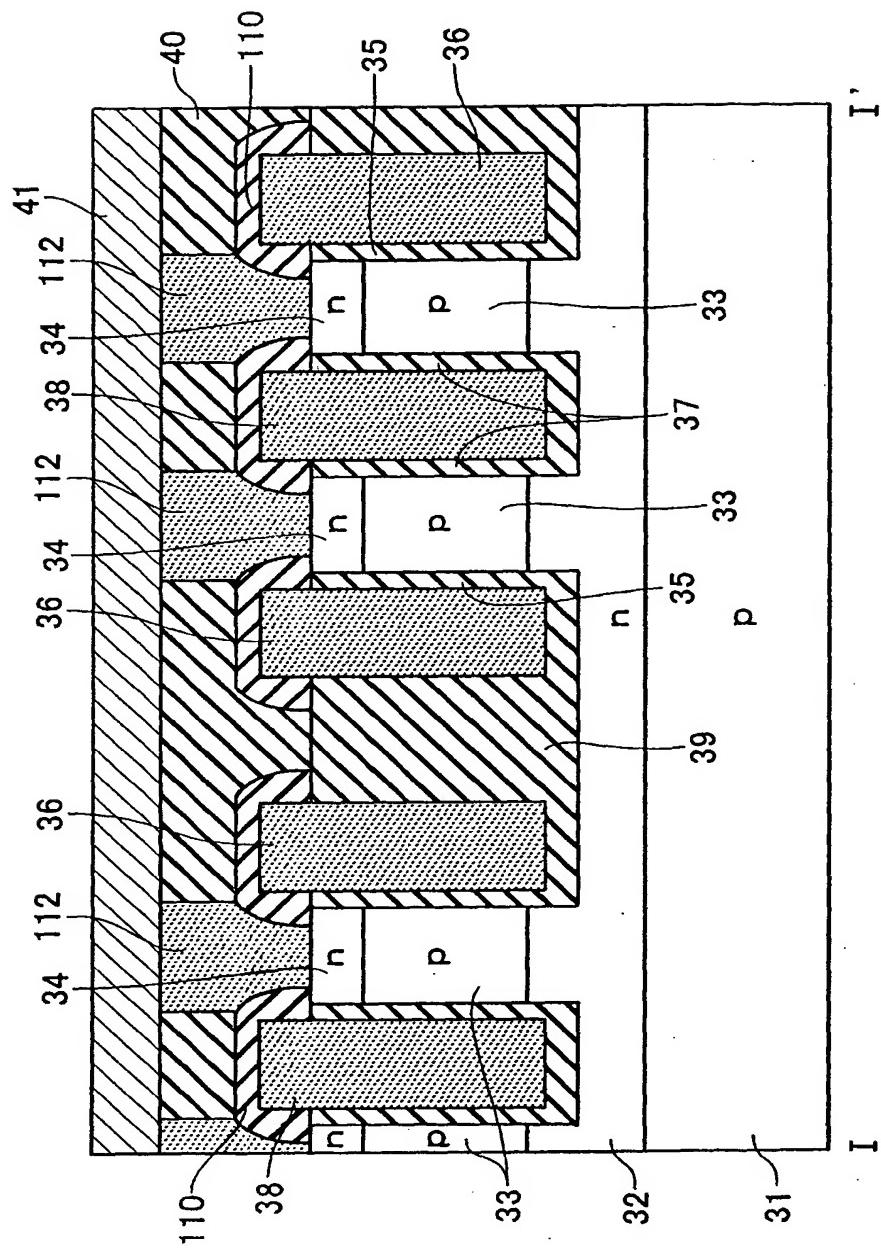


FIG. 26

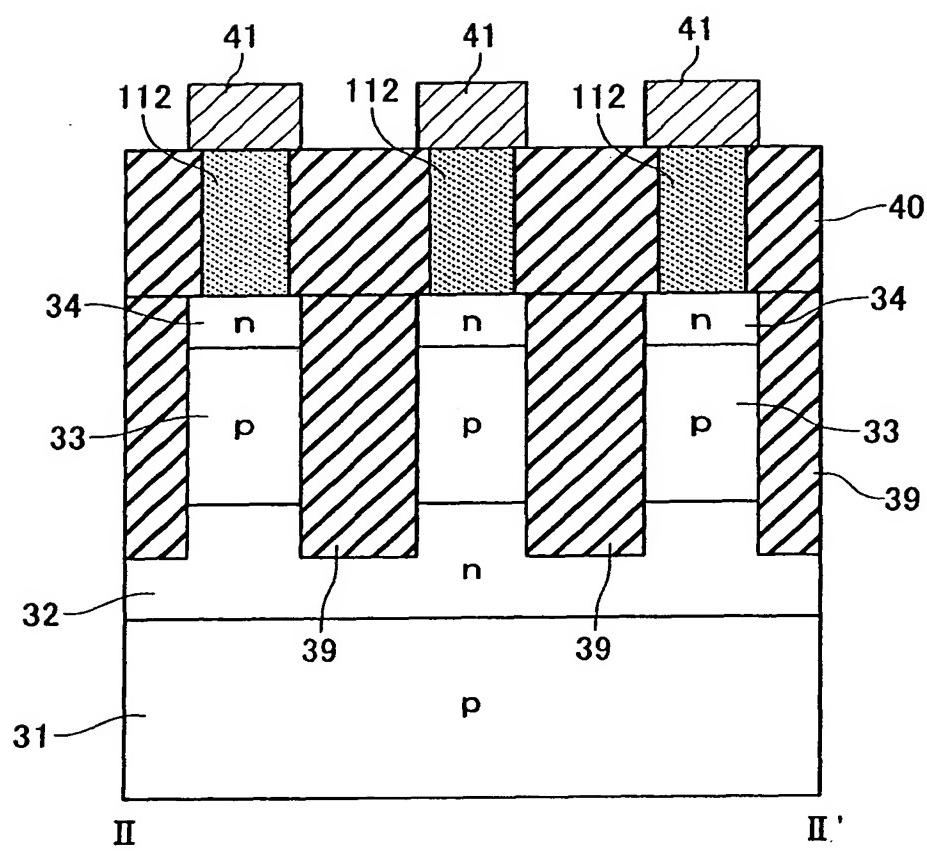


FIG. 27

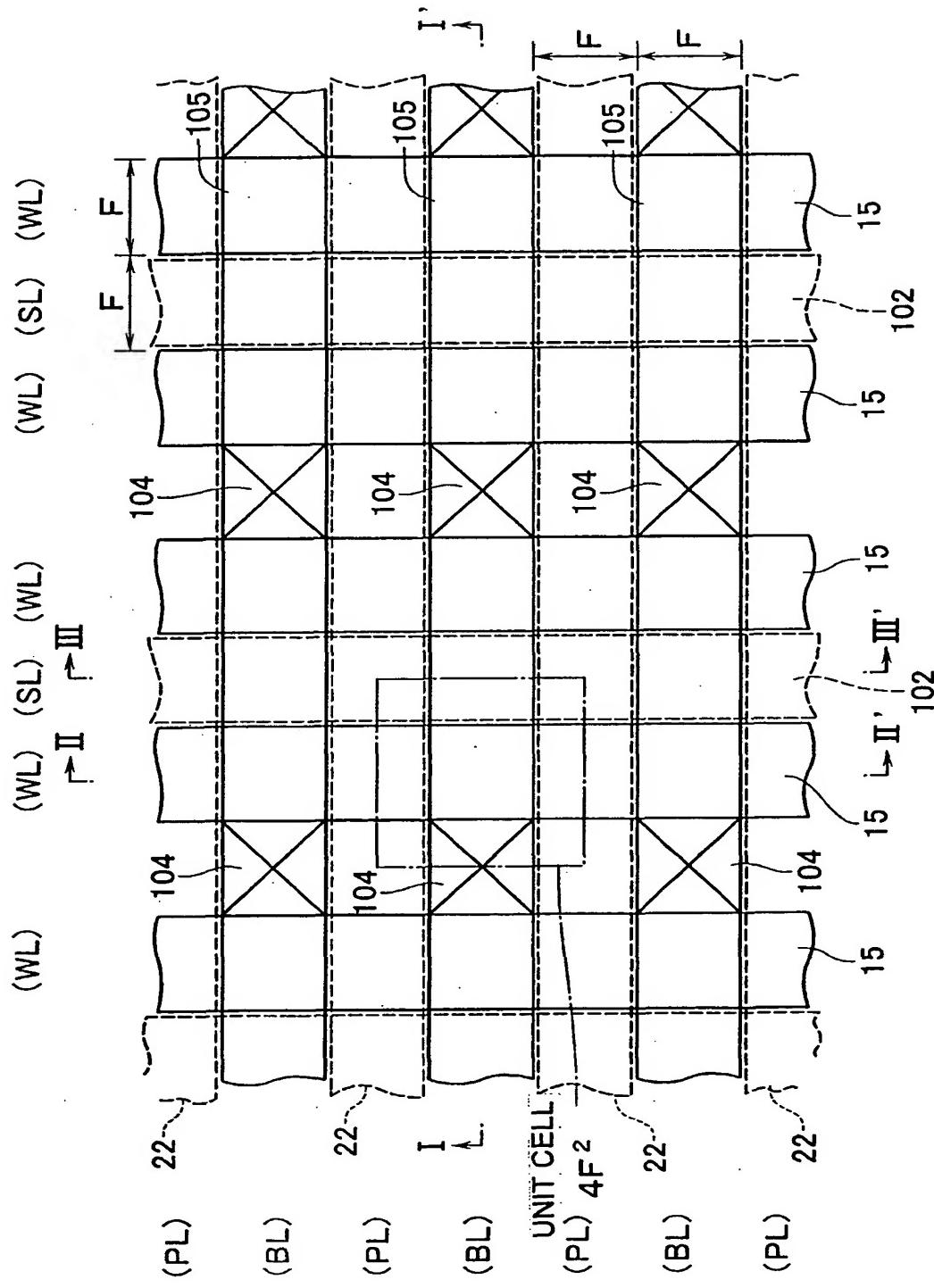


FIG. 28

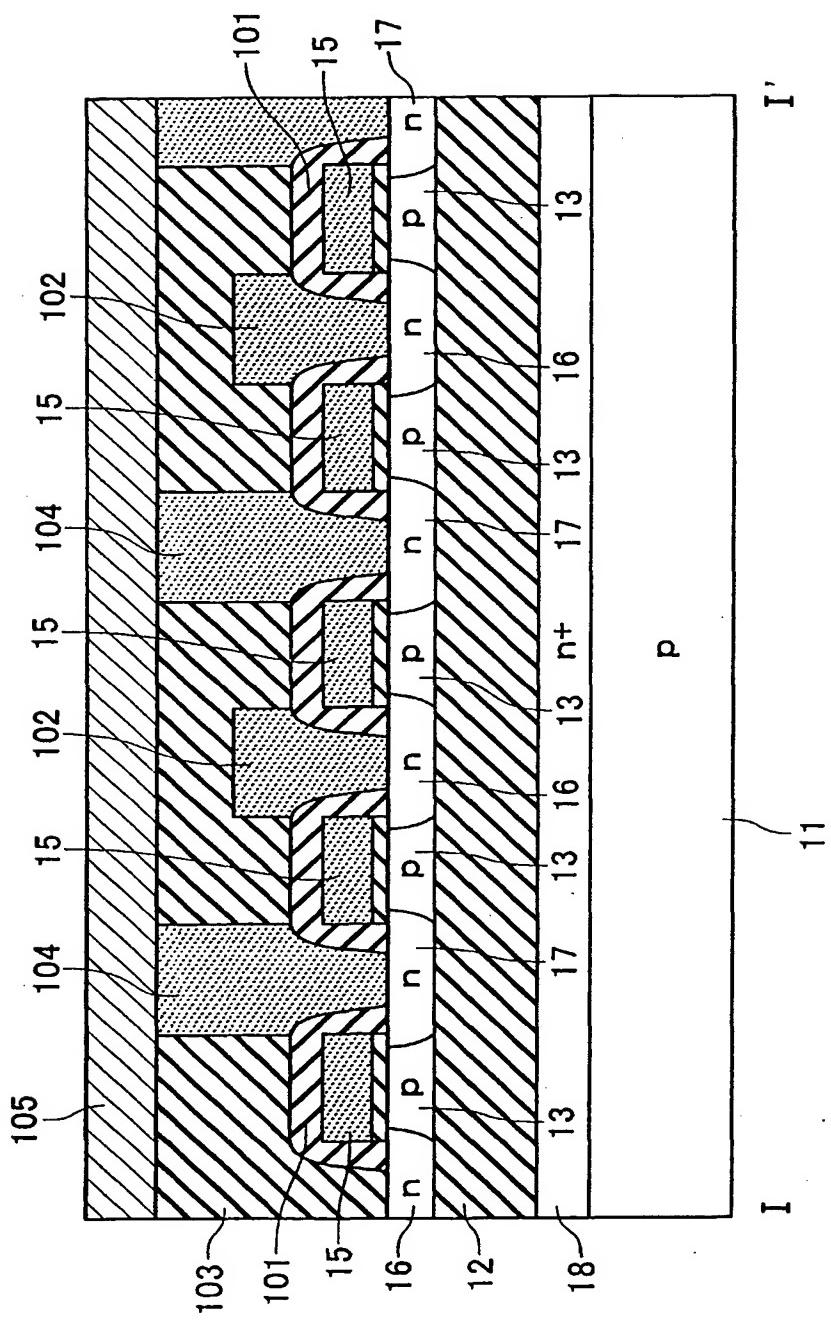


FIG. 29

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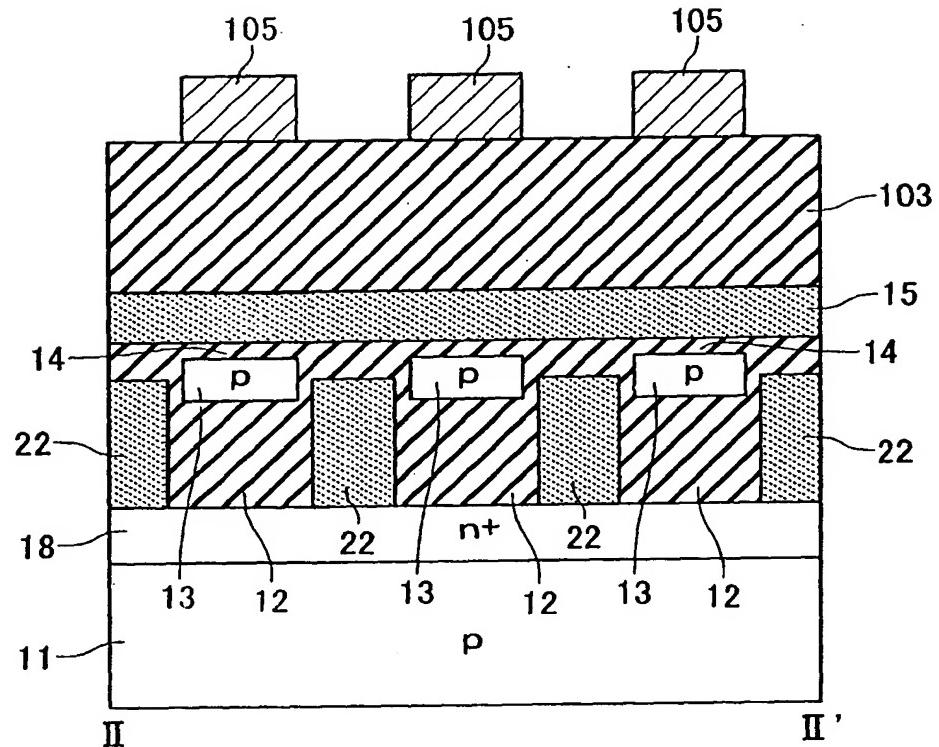


FIG. 30

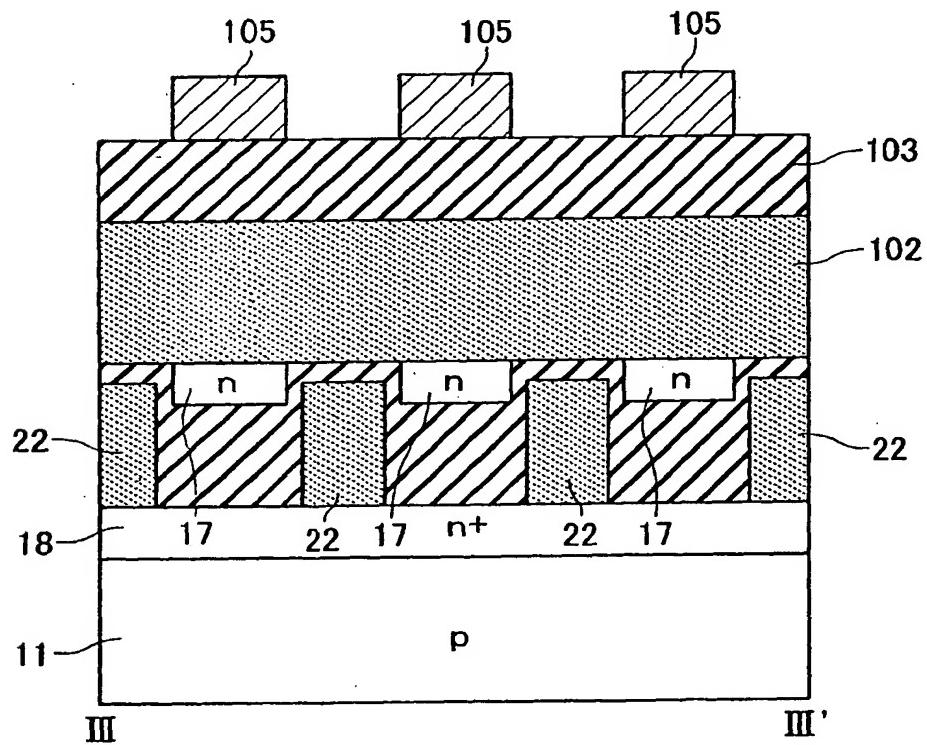


FIG. 31

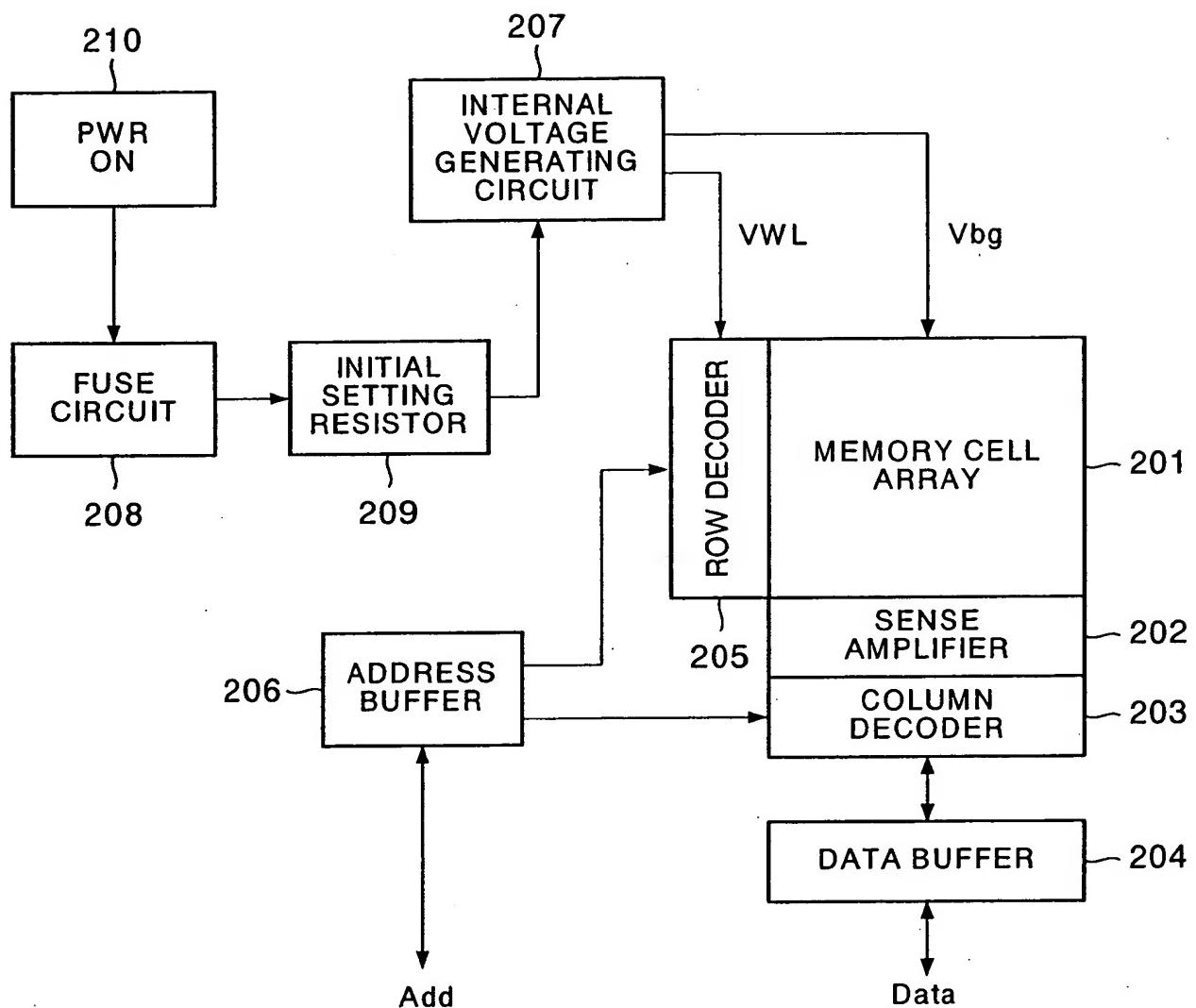


FIG. 32